

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization International Bureau



(43) International Publication Date
11 August 2005 (11.08.2005)

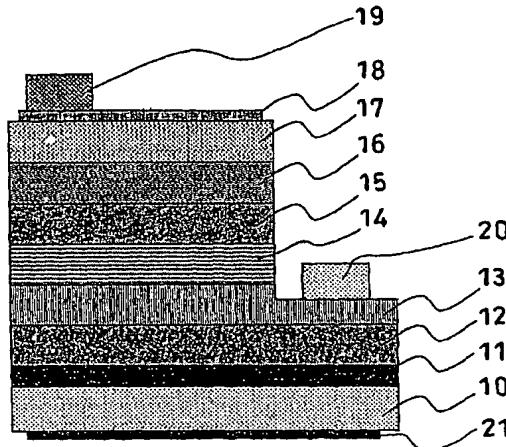
PCT

(10) International Publication Number
WO 2005/074046 A1

- (51) International Patent Classification⁷: **H01L 33/00**
- (21) International Application Number: **PCT/JP2005/001645**
- (22) International Filing Date: 28 January 2005 (28.01.2005)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
2004-022668 30 January 2004 (30.01.2004) JP
60/542,473 9 February 2004 (09.02.2004) US
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,

[Continued on next page]

(54) Title: GALLIUM NITRIDE-BASED COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE



WO 2005/074046 A1

(57) Abstract: A gallium nitride compound semiconductor light-emitting device includes a crystalline substrate (10), a light-emitting layer (15) of a quantum well structure which is formed of a gallium nitride compound semiconductor barrier layer and a gallium nitride compound semiconductor well layer, which light-emitting layer is provided on a second side of the crystalline substrate, a contact layer (17) formed of a Group III-V compound semiconductor for providing an Ohmic electrode for supplying device operation current to the light-emitting layer, and an Ohmic electrode (18) which is provided on the contact layer and has an aperture through which a portion of the contact layer is exposed. The Ohmic electrode exhibits light permeability with respect to light emitted from the light-emitting layer. The well layer contains a thick portion having a large thickness and a thin portion having a small thickness.



SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, ML, MR, NE, SN, TD, TG).

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Published:

— *with international search report*